

WHAT IS CLAIMED IS

1. A method for forming spacers of a micro-display comprising the following steps:

(1) providing a substrate on which reflective pads are formed, 5
the pads being spaced from each other by non-reflective areas;

(2) forming a coating of transparent, non-conductive material on the substrate and over the reflective pads;

(3) providing a mask comprising a number of shielded zones corresponding to the non-reflective areas; and 10

(4) performing a lithographic operation on the transparent, non-conductive coating of step (2) by using the mask of step (3) whereby portions of the transparent, non-conductive material that are corresponding to the shielded zones of the mask are left on the substrate, 15 functioning as spacers.

2. The method as claimed in Claim 1, wherein the transparent, non-conductive material comprises SiO_x .

3. The method as claimed in Claim 2, wherein the SiO_x comprises SiO_2 .

20 4. The method as claimed in Claim 1, wherein the transparent, non-conductive material comprises SiN_x .

5. The method as claimed in Claim 4, wherein the SiN_x comprises SiN_2 .

6. A method for forming spacers of at least two micro-displays of a displaying device comprising the following steps:
 - (1) providing a substrate for each of the at least two micro-displays with reflective pads formed on the substrate, the pads being spaced from each other by non-reflective areas;
 - (2) forming a coating of transparent, non-conductive material on the substrate and over the reflective pads;
 - (3) providing a mask associated with each substrate, each mask comprising a number of shielded zones that are not corresponding in location to each other; and
 - (4) performing a lithographic operation on the transparent, non-conductive coating of each substrate of step (2) by using the associated mask of step (3) whereby portions of the transparent, non-conductive material that are corresponding to the shielded zones of the mask are left on the substrate, functioning as spacers, the spacers of the substrates being not corresponding in location to each other.
7. The method as claimed in Claim 6, wherein the transparent, non-conductive material comprises SiO_x .
8. The method as claimed in Claim 7, wherein the SiO_x comprises SiO_2 .
9. The method as claimed in Claim 6, wherein the transparent, non-conductive material comprises SiN_x .
10. The method as claimed in Claim 9, wherein the SiN_x comprises SiN_2 .

11. The method as claimed in Claim 6, wherein the shielded zones of each mask are arranged to be corresponding to some of the non-reflective areas.

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